

**184pin Unbuffered DIMM
SPD Specification(128Mb B-die base)**

***Rev. 0.4
Jan. 2001***

Revision 0.0 (December 1999)

1. First release for internal use only.

Revision 0.1 (February 2000)

1. First edition for external release.

Revision 0.2 (April 2000)

1. Byte 9, Byte10 : Add tCC and tAC at CL=2.5 in A0 (DDR200@CL=2)and A2(DDR266@CL=2).
2. Byte 23, Bte24 : Add tCC and tAC at CL=2 in B0 (DDR266@CL=2.5).

Revision 0.3 (June 2000)

1. Byte 85 : Changed PCB Revision from T0 to T1.

Revision 0.4 (Jan 2001)

1. Byte 30 : Changed tRAS of B0 from 48ns to 45ns.

SERIAL PRESENCE DETECT

184pin Unbuffered DIMM

M368L3313BT1-CA0/B0/A2

- Organization : 32MX64
- Composition : 16MX8 *8*2
- Used component part # : K4H280838B-TCA0/B0/A2
- # of rows in module : 2 row
- # of banks in component : 4 banks
- Feature : 1,250 mil height & double sided component
- Refresh : 4K/64ms
- Bin Sort : A0 (DDR200@CL=2),B0 (DDR266@CL=2.5), A2(DDR266@CL=2)
- **Contents :**

| Byte # | Function described | Function Supported | | | Hex value | | | Note |
|--------|--|--|--------|--------|-----------|-----|-----|------|
| | | A0 | B0 | A2 | A0 | B0 | A2 | |
| 0 | Defines # of Bytes written into serial memory at module manufacturer | 128bytes | | | 80h | | | |
| 1 | Total # of Bytes of SPD memory device | 256bytes (2K-bit) | | | 08h | | | |
| 2 | Fundamental memory type | SDRAM DDR | | | 07h | | | |
| 3 | # of row address on this assembly | 12 | | | 0Ch | | | 1 |
| 4 | # of column address on this assembly | 10 | | | 0Ah | | | 1 |
| 5 | # of module Rows on this assembly | 2 Row | | | 02h | | | |
| 6 | Data width of this assembly | 64 bits | | | 40h | | | |
| 7 |Data width of this assembly | - | | | 00h | | | |
| 8 | VDDQ and interface standard of this assembly | SSTL 2.5V | | | 04h | | | |
| 9 | DDR SDRAM cycle time at CAS Latency =2.5 | 8ns | 7.5ns | 7ns | 80h | 75h | 70h | 2 |
| 10 | DDR SDRAM Access time from clock at CL=2.5 | ±0.8ns | ±0.75n | ±0.75n | 80h | 75h | 75h | 2 |
| 11 | DIMM configuration type(Non-parity, Parity, ECC) | Non-parity, ECC | | | 00h | | | |
| 12 | Refresh rate & type | 15.6us & Self refresh | | | 80h | | | |
| 13 | Primary DDR SDRAM width | x8 | | | 08h | | | |
| 14 | Error checking DDR SDRAM data width | N/A | | | 00h | | | |
| 15 | Minimum clock delay for back-to-back random column address | tCCD=1CLK | | | 01h | | | |
| 16 | DDR SDRAM device attributes : Burst lengths supported | 2,4,8 | | | 0Eh | | | |
| 17 | DDR SDRAM device attributes : # of banks on each DDR SDRAM | 4 banks | | | 04h | | | |
| 18 | DDR SDRAM device attributes : CAS Latency supported | 2,2.5 | | | 0Ch | | | |
| 19 | DDR SDRAM device attributes : CS Latency | 0CLK | | | 01h | | | |
| 20 | DDR SDRAM device attributes : WE Latency | 1CLK | | | 02h | | | |
| 21 | DDR SDRAM module attributes | Registered address& control inputs and On-card DLL | | | 20h | | | |
| 22 | DDR SDRAM device attributes : General | +/-0.2V voltage tolerance | | | 00h | | | |
| 23 | DDR SDRAM cycle time at CL =2 | 10ns | 10ns | 7.5ns | A0h | A0h | 75h | 2 |
| 24 | DDR SDRAM Access time from clock at CL =2 | ±0.8ns | ±0.75n | ±0.75 | 80h | 75h | 75h | 2 |
| 25 | DDR SDRAM cycle time at CL =1.5 | - | - | - | 00h | | | 2 |
| 26 | DDR SDRAM Access time from clock at CL =1.5 | - | - | - | 00h | | | 2 |
| 27 | Minimum row precharge time (=tRP) | 20ns | 20ns | 20ns | 50h | 50h | 50h | |
| 28 | Minimum row activate to row active delay(=tRRD) | 15ns | 15ns | 15ns | 3Ch | 3Ch | 3Ch | |
| 29 | Minimum RAS to CAS delay(=tRCD) | 20ns | 20ns | 20ns | 50h | 50h | 50h | |
| 30 | Minimum active to precharge time(=tRAS) | 48ns | 45ns | 45ns | 30h | 2Dh | 2Dh | |
| 31 | Module ROW density | 128MB | | | 20h | | | |
| 32 | Command and address signal input setup time | 1.1ns | 0.9ns | 0.9ns | B0h | 90h | 90h | |
| 33 | Command and address signal input hold time | 1.1ns | 0.9ns | 0.9ns | B0h | 90h | 90h | |
| 34 | Data signal input setup time | 0.6ns | 0.5ns | 0.5ns | 60h | 50h | 50h | |

SERIAL PRESENCE DETECT

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SERIAL PRESENCE DETECT INFORMATION

| Byte # | Function described | Function Supported | | | Hex value | | | Note |
|---------|---|--------------------|-------|-------|-----------|-----|-----|------|
| | | A0 | B0 | A2 | A0 | B0 | A2 | |
| 35 | Data signal input hold time | 0.6ns | 0.5ns | 0.5ns | 60h | 50h | 50h | |
| 36-61 | Superset information (may be used in future) | - | | | 00h | | | |
| 62 | SPD data revision code | Initial release | | | 00h | | | |
| 63 | Checksum for Bytes 0 ~ 62 | - | | | 21h | 9Dh | 6Dh | |
| 64 | Manufacturer JEDEC ID code | Samsung | | | CEh | | | |
| 65 - 71 | Manufacturer JEDEC ID code | Samsung | | | 00h | | | |
| 72 | Manufacturing location | Onyang Korea | | | 01h | | | |
| 73 | Manufacturer part # (Memory Module) | M | | | 4Dh | | | |
| 74 | Manufacturer part # (DIMM Configuraion) | 3 | | | 33h | | | |
| 75 | Manufacturer part # (Data bits & Module type) | Blank | | | 20h | | | |
| 76 | Manufacturer part # (Data bits & Module type) | 6 | | | 36h | | | |
| 77 | Manufacturer part # (Data bits & Module type) | 8 | | | 38h | | | |
| 78 | Manufacturer part # (Operating Voltage) | L | | | 4Ch | | | |
| 79 | Manufacturer part # (Module depth) | 3 | | | 33h | | | |
| 80 | Manufacturer part # (Module depth) | 3 | | | 33h | | | |
| 81 | Manufacturer part # (Refresh, # of rows in comp.&interface) | 1 | | | 31h | | | |
| 82 | Manufacturer part # (Composition component) | 3 | | | 33h | | | |
| 83 | Manufacturer part # (Component Revision) | B-die | | | 42h | | | |
| 84 | Manufacturer part # (Package type) | T | | | 54h | | | |
| 85 | Manufacturer part # (PCB Revision) | 1 | | | 31h | | | |
| 86 | Manufacturer part # (Hyphen) | "-" | | | 2Dh | | | |
| 87 | Manufacturer part # (Power) | C | | | 43h | | | |
| 88 | Manufacturer part # (Minimum cycle time) | A | B | A | 41h | 42h | 41h | |
| 89 | Manufacturer part # (Minimum cycle time) | 0 | 0 | 2 | 30h | 30h | 32h | |
| 90 | Manufacturer part # (T.B.D) | Blank | | | 20h | | | |
| 91 | Manufacturer revision code (For PCB) | 0 | | | 30h | | | |
| 92 | Manufacturer revision code (For component) | B-die | | | 42h | | | |
| 93 | Manufacturing date (Week) | - | | | - | | | 3 |
| 94 | Manufacturing date (Year) | - | | | - | | | 3 |
| 95~98 | Assembly serial # | - | | | - | | | 4 |
| 99~127 | Manufacturer specific data (may be used in future) | Undefined | | | 00h | | | 5 |
| 128~255 | Open for customer use | Undefined | | | 00h | | | 5 |

- Note :**
1. The bank select address is excluded in counting the total # of addresses.
 2. This value is based on the component specification.
 3. These bytes are programmed by code of Date Week & Date Year.
 4. These bytes are programmed by Samsung 's own Assembly Serial # system. All modules may have different unique serial #.
 5. These bytes are Undefined and coded with 00h'.